

Form PTO-1449  
(Rev. 8-83)U.S. Department of Commerce  
Patent and Trademark Office

Attorney Docket No. 0756-1880

Serial No. New Application

**INFORMATION DISCLOSURE STATEMENT**

(Use several sheets if necessary)

Applicant: Takashi INUSHIMA et al

Filing Date: November 10, 1998

Group: 1762

jc549 U.S. Pat. & Tm. Office  
09/188382  
11/10/98

**U.S. PATENT DOCUMENTS**

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
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	4,872,947	10/10/89	Wang et al	216	38	
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	5,354,715	10/11/94	Wang et al	438	699	
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	4,282,268	08/04/81	Priestley et al	427	579	06/06/78
	4,419,385	12/06/83	Peters	427	99	09/24/81
	4,567,352	01/28/86	Mimura et al	219	405	
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	3,026,435	03/20/62	McPherson	313	22	
	3,665,235	05/23/72	Hugot	313	24	
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Examiner <i>Passa-It</i>	Date Considered <i>1-7-99</i>					

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	59-194452	11/05/84	Japan			Abstract	
	59-82732	05/12/84	Japan			Abstract	
	62-188375	08/17/87	Japan			Abstract	
	61-234531	10/18/86	Japan			Abstract	
	62-054940	03/10/87	Japan			Abstract	
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	61-063020	1986	Japan				X
	60-167318	08/30/85	Japan				X
	2-219232	08/31/90	Japan				X
	182797	09/06/66	USSR	313	22		X
	60-245217	05/12/85	Japan	—	—		X
	61-65419	04/04/86	Japan	118	725		X
	61-210622	09/18/86	Japan	118	725		X
	62-80272	04/13/87	Japan	118	725		X
	62-160462	07/16/87	Japan	118	725		X
	63-147314	06/20/88	Japan				X
	61-063020	04/01/86	Japan				X
	60-167318	08/30/85	Japan				X
	2-219232	08/31/90	Japan				X

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